

G1332E**N-CHANNEL ENHANCEMENT MODE POWER MOSFET**

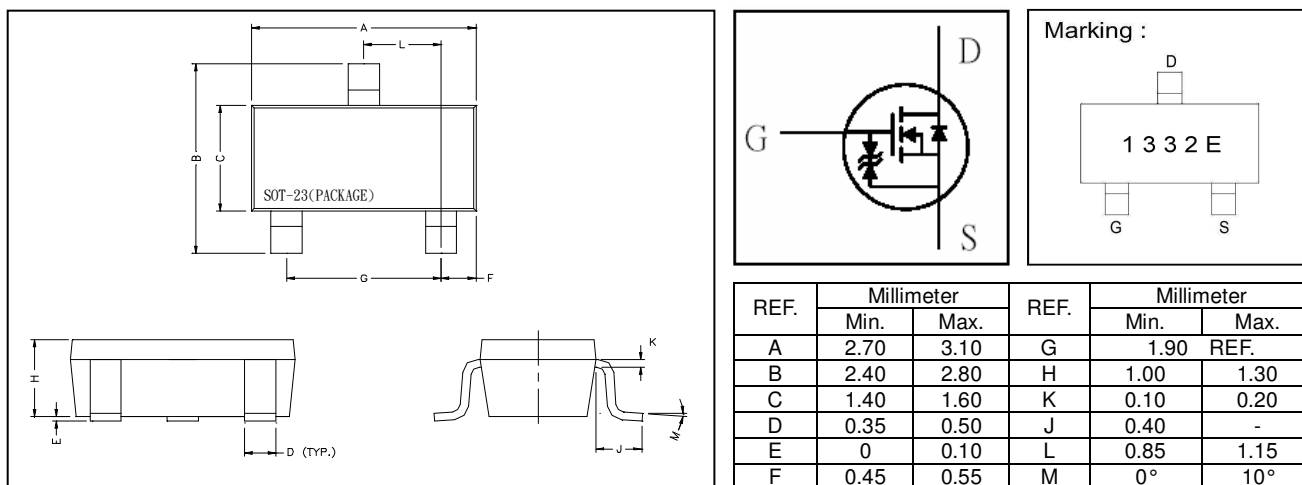
| | |
|---------|-------|
| BVDSS | 20V |
| RDS(ON) | 600mΩ |
| ID | 600mA |

Description

The G1332E provide the designer with best combination of fast switching, low on-resistance and cost-effectiveness.

Features

- *Simple Gate Drive
- *Small Package Outline
- *2KV ESD Rating (Per MIL-STD-883D)

Package Dimensions**Absolute Maximum Ratings**

| Parameter | Symbol | Ratings | Unit |
|--|------------------------|------------|------|
| Drain-Source Voltage | V_{DS} | 20 | V |
| Gate-Source Voltage | V_{GS} | ±5 | V |
| Continuous Drain Current ³ | $I_D @ TA=25^{\circ}C$ | 600 | mA |
| Continuous Drain Current ³ | $I_D @ TA=70^{\circ}C$ | 470 | mA |
| Pulsed Drain Current ^{1,2} | I_{DM} | 2.5 | A |
| Total Power Dissipation | $P_D @ TA=25^{\circ}C$ | 1.0 | W |
| Linear Derating Factor | | 0.008 | W/°C |
| Operating Junction and Storage Temperature Range | T_j, T_{stg} | -55 ~ +150 | °C |

Thermal Data

| Parameter | Symbol | Value | Unit |
|---|-------------|-------|------|
| Thermal Resistance Junction-ambient ³ Max. | R_{thj-a} | 125 | °C/W |

Electrical Characteristics (T_j = 25°C unless otherwise specified)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Test Conditions |
|--|--------------------------------|------|------|------|------|--|
| Drain-Source Breakdown Voltage | BV _{DSS} | 20 | - | - | V | V _{GS} =0, I _D =250uA |
| Breakdown Voltage Temperature Coefficient | $\Delta BV_{DSS} / \Delta T_j$ | - | 0.02 | - | V/°C | Reference to 25°C, I _D =1mA |
| Gate Threshold Voltage | V _{GS(th)} | 0.5 | - | 1.2 | V | V _{DS} =V _{GS} , I _D =250uA |
| Forward Transconductance | g _{fs} | - | 1 | - | S | V _{DS} =5V, I _D =600mA |
| Gate-Source Leakage Current | I _{GSS} | - | - | ±10 | uA | V _{GS} = ±5V |
| Drain-Source Leakage Current(T _j =25°C) | I _{DSS} | - | - | 1 | uA | V _{DS} =20V, V _{GS} =0 |
| Drain-Source Leakage Current(T _j =70°C) | | - | - | 10 | uA | V _{DS} =16V, V _{GS} =0 |
| Static Drain-Source On-Resistance | R _{DS(ON)} | - | - | 600 | mΩ | V _{GS} =4.5V, I _D =600mA |
| | | - | - | 1200 | | V _{GS} =2.5V, I _D =400mA |
| Total Gate Charge ² | Q _g | - | 1.3 | 2 | nC | I _D =600mA V _{DS} =16V V _{GS} =4.5V |
| Gate-Source Charge | Q _{gs} | - | 0.3 | - | | |
| Gate-Drain ("Miller") Charge | Q _{gd} | - | 0.5 | - | | |
| Turn-on Delay Time ² | T _{d(on)} | - | 4 | - | ns | V _{DS} =10V I _D =600mA V _{GS} =10V R _G =3.3Ω R _D =16.7Ω |
| Rise Time | T _r | - | 10 | - | | |
| Turn-off Delay Time | T _{d(off)} | - | 15 | - | | |
| Fall Time | T _f | - | 2 | - | | |
| Input Capacitance | C _{iss} | - | 38 | 60 | pF | V _{GS} =0V V _{DS} =10V f=1.0MHz |
| Output Capacitance | C _{oss} | - | 17 | - | | |
| Reverse Transfer Capacitance | C _{rss} | - | 12 | - | | |

Source-Drain Diode

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Test Conditions |
|---------------------------------|-----------------|------|------|------|------|--|
| Forward On Voltage ² | V _{SD} | - | - | 1.2 | V | I _S =300mA, V _{GS} =0V |

Notes: 1. Pulse width limited by Max. junction temperature.

2. Pulse width ≤ 300us, duty cycle ≤ 2%.

3. Surface mounted on FR4 board, t ≤ 10sec.

Characteristics Curve

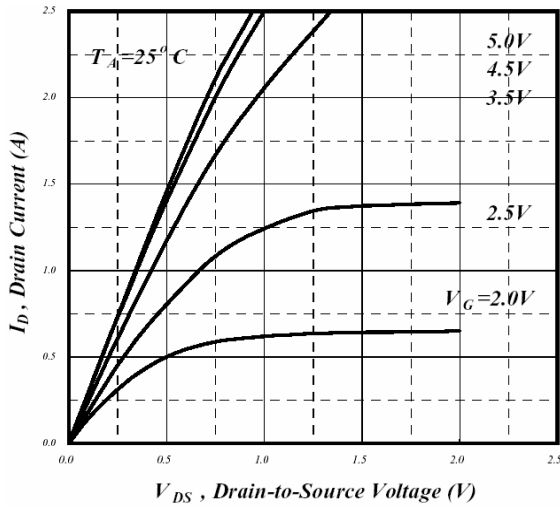


Fig 1. Typical Output Characteristics

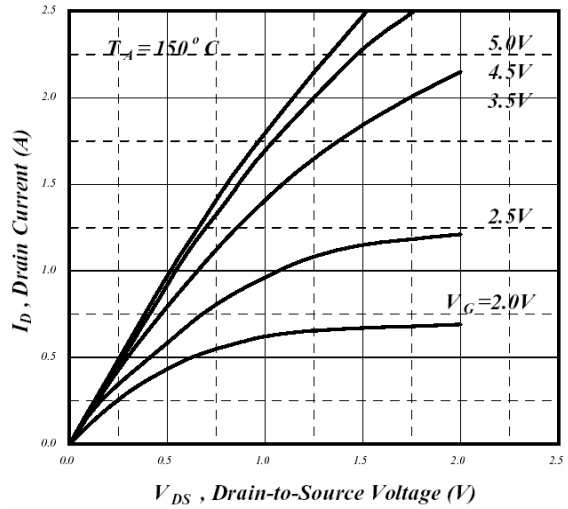


Fig 2. Typical Output Characteristics

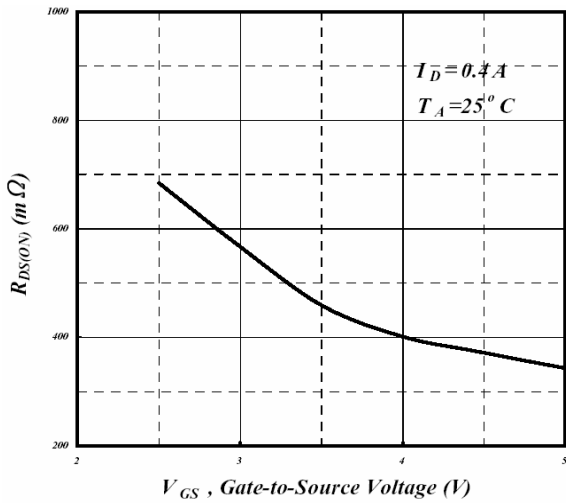


Fig 3. On-Resistance v.s. Gate Voltage

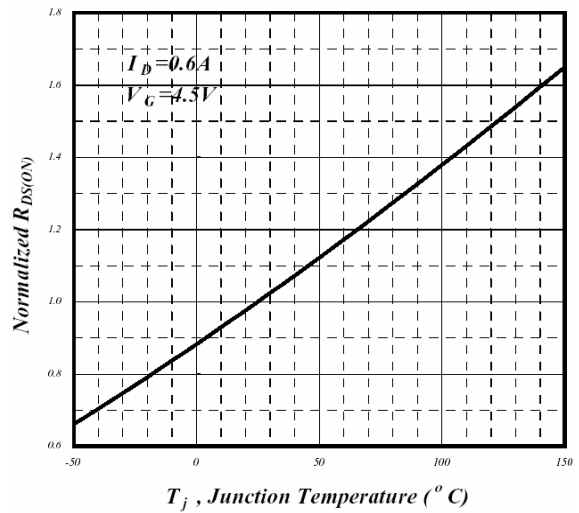


Fig 4. Normalized On-Resistance v.s. Junction Temperature

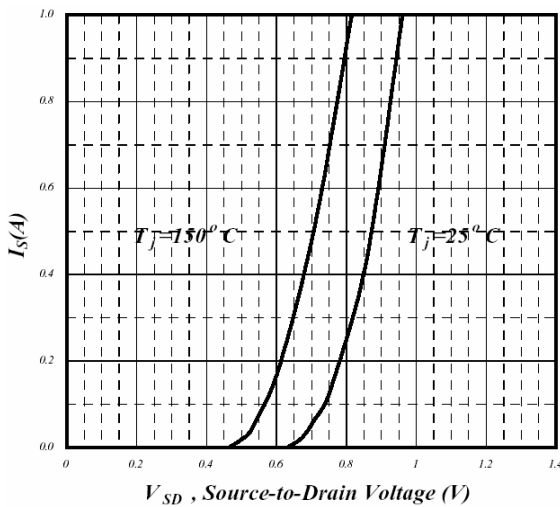


Fig 5. Forward Characteristics of Reverse Diode

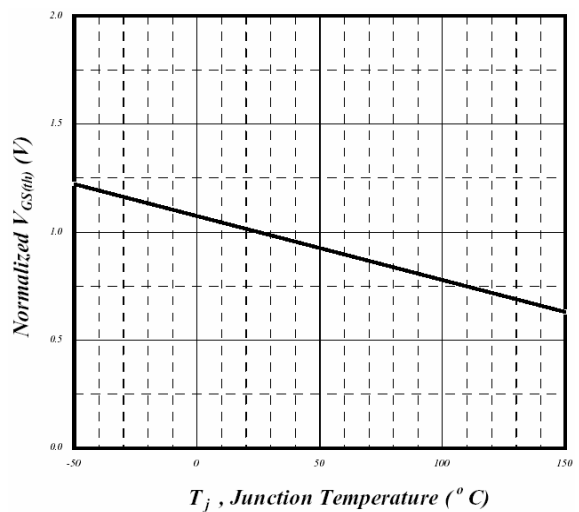


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

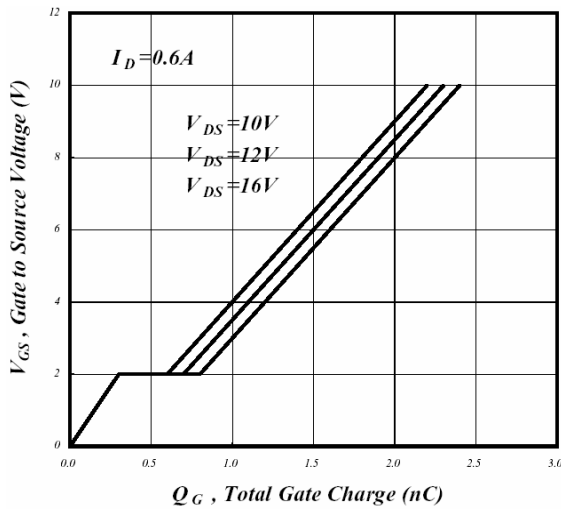


Fig 7. Gate Charge Characteristics

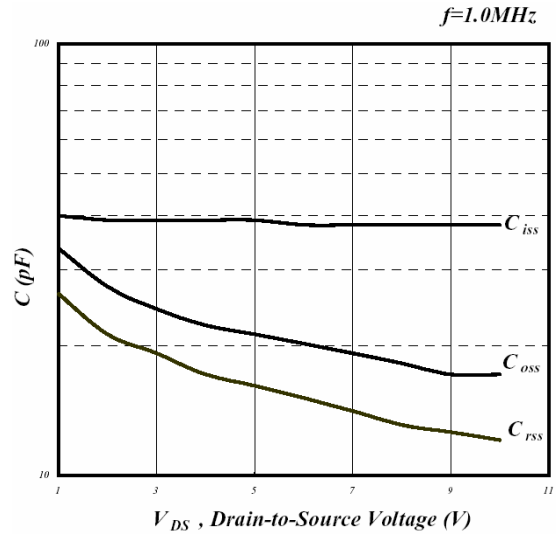


Fig 8. Typical Capacitance Characteristics

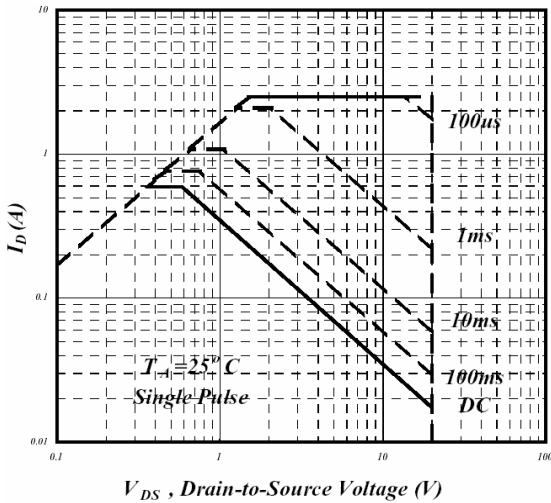


Fig 9. Maximum Safe Operating Area

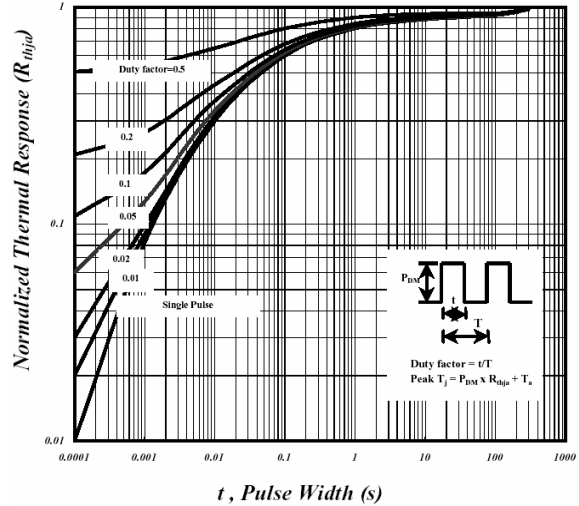


Fig 10. Effective Transient Thermal Impedance

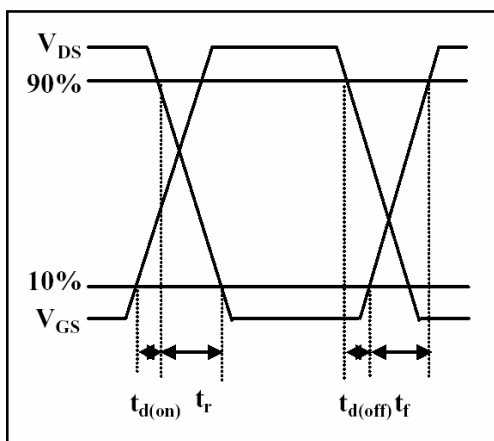


Fig 11. Switching Time Waveform

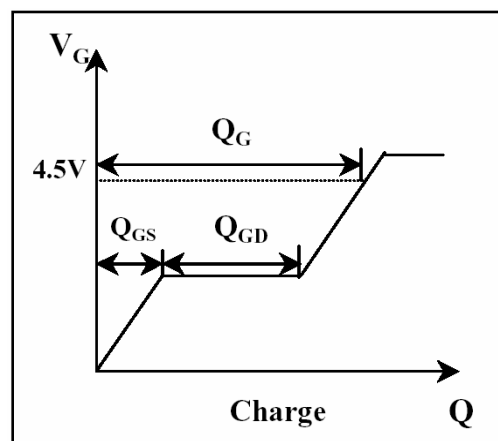


Fig 12. Gate Charge Waveform

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